

HIGH-SPEED 2.5V 1024K x 36 SYNCHRONOUS DUAL-PORT STATIC RAM WITH 3.3V OR 2.5V INTERFACE

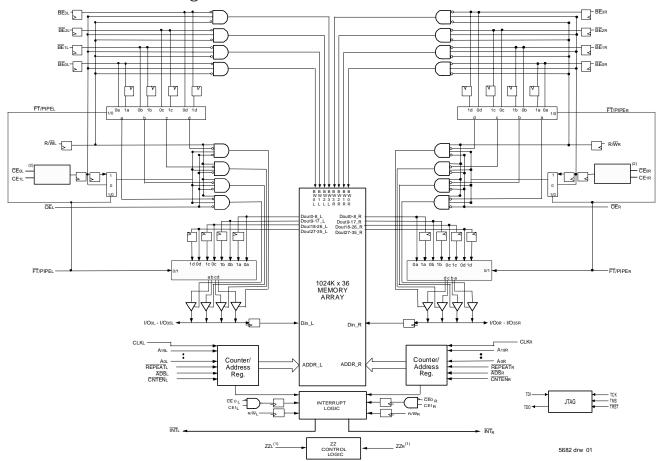
IDT70T3509M

Features:

- True Dual-Port memory cells which allow simultaneous access of the same memory location
- High-speed data access
 - Commercial: 4.2ns (133MHz)(max.)
 - Industrial: 4.2ns (133MHz)(max.)
- Selectable Pipelined or Flow-Through output mode
- Counter enable and repeat features
- Interrupt Flags
- Full synchronous operation on both ports
 - 7.5ns cycle time, 133MHz operation (9.5Gbps bandwidth)
 - 1.5ns setup to clock and 0.5ns hold on all control, data, and address inputs @ 133MHz
 - Fast 4.2ns clock to data out

- Data input, address, byte enable and control registers
- Self-timed write allows fast cycle time
- Separate byte controls for multiplexed bus and bus matching compatibility
- Dual Cycle Deselect (DCD) for Pipelined Output Mode
- 2.5V (±100mV) power supply for core
- LVTTL compatible, selectable 3.3V (±150mV) or 2.5V (±100mV) power supply for I/Os and control signals on each port
- Includes JTAG functionality
- Available in a 256-pin Ball Grid Array (BGA)
- Common BGA footprint provides design flexibility over seven density generations (512K to 36M-bit)
- Green parts available, see ordering information

Functional Block Diagram



NOTE:

- The sleep mode pin shuts off all dynamic inputs, except JTAG inputs, when asserted. All static inputs, i.e., PL/FTx and OPTx and the sleep mode pins themselves (ZZx) are not affected during sleep mode.
- 2. See Truth Table I for Functionality.

AUGUST 2007

Description:

The IDT70T3509M is a high-speed 1024K x 36 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT70T3509M has been optimized for applications having unidirectional

or bidirectional data flow in bursts. An automatic power down feature, controlled by $\overline{\text{CE}}$ 0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode.

The 70T3509M can support an operating voltage of either 3.3V or 2.5V on one or both ports, controllable by the OPT pins. The power supply for the core of the device (VDD) is at 2.5V.

Pin Configuration (1,2,3,4)

70T3509M BP BP-256^(5,7)

256-Pin BGA Top View⁽⁶⁾

08/03/04

A1	A2	A3	A4	A5	A6	A7	A8	A9	A10	A11	A12	A13	A14	A15	A16
NC	TDI	A19L	A17L	A14L	A11L	A8L	BE ₂ L	CE1L	OEL	CNTENL	A 5L	A2L	A0L	NC	NC
B1	B2	B3	B4	B5	B6	B7	B8	B9	B10	B11	B12	B13	B14	B15	B16
I/O18L	NC	TDO	A 18L	A15L	A12L	A9L	BE3L	CE ₀ L	R/WL	REPEATL	A4L	A1L	VDD	I/O17L	NC
C1	C2	C3	C4	C5	C6	C7	C8	C9	C10	C11	C12	C13	C14	C15	C16
I/O18R	I/O19L	Vss	A16L	A13L	A10L	A7L	BE ₁ L	BE ₀ L	CLKL	ADSL	A6L	A3L	OPTL	I/O17R	I/O16L
D1	D2	D3	D4	d5	d6	d7	d8	d9	d10	d11	D12	D13	D14	D15	D16
I/O20R	I/O19R	I/ O 20L	PIPE/FTL	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	VDD	I/O15R	I/O15L	I/O16R
E1		E3	E4	E5	E6	E7	E8	E9	E10	E11	E12	E13	E14	E15	E16
I/O21R		I/O22L	Vddql	Vdd	Vdd	ĪNTL	Vss	Vss	Vss	VDD	Vdd	Vddqr	I/O13L	I/O14L	I/O14R
F1	F2	F3	f4	F5	F6	F7	F8	F9	F10	F11	F12	F13	F14	F15	F16
I/O23L	I/ O 22R	I/ O 23R	Vddql	Vdd	NC	NC	Vss	Vss	Vss	Vss	Vdd	Vddqr	I/O12R	I/O13R	I/O12L
G1	G2	G3	G4	G5	G6	G7	G8	_{G9}	G10	G11	G12	G13	G14	G15	G16
I/O24R	I/O24L	I/ O 25L	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	I/O10L	I/O11L	I/O11R
H1	H2	H3	h4	H5	H6	H7	H8	H9	H10	H11	H12	H13	H14	H15	H16
I/O26L	I/O 25R	I/O26R	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	I/O9R	IO 9L	I/O10R
J1	J2	J3	J4	J5	J6	J7	J8	^{J9}	J10	J11	J12	J13	J14	J15	J16
I/O27L	I/ O 28R	I/ O 27R	Vddql	ZZR	Vss	Vss	Vss	Vss	Vss	Vss	ZZ L	Vddqr	I/O8R	I/ O 7R	I/O8L
K1	K2	K3	K4	K5	K6	K7	K8	K9	K10	K11	K12	K13	K14	K15	K16
I/O29R	I/ O 29L	I/O28L	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	I/O6R	I/O6L	I/O7L
L1	L2	L3	L4	L5	L6	L7	L8	L9	L10	L11	L12	L13	L14	L15	L16
I/O30L	I/O31R	I/ O 30R	Vddqr	VDD	NC	NC	Vss	Vss	Vss	Vss	Vdd	Vddql	I/O5L	I/O4R	I/O5R
M1	M2	M3	m4	M5	M6	M7	M8	м9	M10	M11	M12	M13	M14	M15	M16
I/O32R	I/O32L	I/O31L	Vddqr	Vdd	Vdd	ĪNTR	Vss	Vss	Vss	VDD	Vdd	Vddql	I/O3R	I/O3L	I/O4L
N1	N2	N3	N4	n5	n6	n7	n8	n9	N10	N11	N12	N13	N14	N15	N16
I/O33L	I/O34R	I/ O 33R	PIPE/FTR	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vdd	I/O2L	I/O1R	I/O2R
P1		P3	P4	P5	P6	P7	P8	P9	P10	P11	P12	P13	P14	P15	P16
I/O35R		TMS	A16R	A13R	A10R	A 7R	BE1R	BE0R	CLKR	ADSR	A6R	A 3R	I/OoL	I/O0R	I/O1L
R1	R2	R3	R4	R5	R6	R7	R8	R9	R10	R11	R12	R13	R14	R15	R16
I/O35L	NC	TRST	A 18R	A15R	A12R	A 9R	BE3R	CEor	R/W R	REPEATR	A4R	A1R	OPTR	NC	NC
T1	T2	T3	T4	T5	T6	T7	T8	T9	T10	T11	T12	T13	T14	T15	T16
NC	TCK	A 19R	A17R	A 14R	A 11R	A8R	BE2R	CE1R	OEr	CNTENR	A 5R	A2R	Aor	NC	NC

5682 drw 02d

- 1. All VDD pins must be connected to 2.5V power supply.
- 2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VDD (2.5V), and 2.5V if OPT pin for that port is set to Vss (0V).
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 17mm x 17mm x 1.76mm, with 1.0mm ball-pitch.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.
- 7. BP-256 package thickness is 1.76mm nominal. This is thicker than the BC-256 package (1.40mm nominal) used for the lower density IDT dual-port products.

Pin Names

Left Port	Right Port	Names			
CEOL, CE1L	CEOR, CE1R	Chip Enables (Input) ⁽⁵⁾			
R/WL	R/W̄R	Read/Write Enable (Input)			
ŌĒL ŌĒR		Output Enable (Input)			
Aol - A19L	A0R - A19R	Address (Input)			
I/Ool - I/O35L	I/Oor - I/O35R	Data Input/Output			
CLKL	CLKR	Clock (Input)			
PL/ FT L	PL/FT _R	Pipeline/Flow-Through (Input)			
ADSL	ADS R	Address Strobe Enable (Input)			
CNTEN _L CNTEN _R		Counter Enable (Input)			
REPEATL REPEATR		Counter Repeat ⁽³⁾ (Input)			
BEOL - BE3L	BEOR - BE3R	Byte Enables (9-bit bytes) (Input) ⁽⁵⁾			
VDDQL	VDDQR	Power (I/O Bus) (3.3V or 2.5V) ⁽¹⁾ (Input)			
OPTL	OPTR	Option for selecting VDDQx ^(1,2) (Input)			
ZZL	ZZ R	Sleep Mode pin ⁽⁴⁾ (Input)			
,	Vdd	Power (2.5V) ⁽¹⁾ (Input)			
,	Vss	Ground (0V) (Input)			
	TDI	Test Data Input			
-	TDO	Test Data Output			
	TCK	Test Logic Clock (10MHz) (Input)			
-	TMS	Test Mode Select (Input)			
Ī	RST	Reset (Initialize TAP Controller) (Input)			
ĪNTL	ĪN₹R	Interrupt Flag (Output)			

- 1. VDD, OPTx, and VDDQx must be set to appropriate operating levels prior to applying inputs on the I/Os and controls for that port.
- 2. OPTx selects the operating voltage levels for the I/Os and controls on that port. If OPTx is set to VDD (2.5V), then that port's I/Os and controls will operate at 3.3V levels and VDDOx must be supplied at 3.3V. If OPTx is set to Vss (0V), then that port's I/Os and address controls will operate at 2.5V levels and VDDQx must be supplied at 2.5V. The OPT pins are independent of one another—both ports can operate at 3.3V levels, both can operate at 2.5V levels, or either can operate at 3.3V with the other at 2.5V.
- 3. When $\overline{\text{REPEAT}}x$ is asserted, the counter will reset to the last valid address loaded via ADSx.
- 4. The sleep mode pin shuts off all dynamic inputs, except JTAG inputs, when asserted. All static inputs, i.e., PL/FTx and OPTx and the sleep mode pins themselves (ZZx) are not affected during sleep mode. It is recommended that boundary scan not be operated during sleep mode.
- 5. Chip Enables and Byte Enables are double buffered when $PL/\overline{FT} = V_{IH}$, i.e., the signals take two cycles to deselect.

Truth Table I—Read/Write and Enable Control (1,2,3,4)

<u> 11 U</u>	<u>tn i</u>	<u>aui</u>	<u>e 1–</u>	-RE	<u>au/\</u>	<u>/ ۷ </u>	e ai	iu c	Hak	<u>ne Co</u>	HUOL	(1,2,5,7)		
ŌĒ	CLK	Œ0	CE ₁	BE ₃	BE ₂	BE ₁	BE ₀	R/W	ZZ	Byte 3 I/O ₂₇₋₃₅	Byte 2 I/O ₁₈₋₂₆	Byte 1 I/O ₉₋₁₇	Byte 0 I/O ₀₋₈	MODE
Х	1	Н	L	Х	Х	Х	Χ	Х	L	High-Z	High-Z	High-Z	High-Z	Deselected-Power Down
Х	1	L	L	Х	Х	Х	Х	Χ	Х	Active	Active	Active	Active	Not Allowed
Х	1	Н	Н	Х	Х	Х	Х	Х	Х	Active	Active	Active	Active	Not Allowed
Х	↑	L	Н	Η	Н	Н	Н	Х	L	High-Z	High-Z	High-Z	High-Z	All Bytes Deselected
Х	↑	L	Н	Ι	Н	Н	L	L	L	High-Z	High-Z	High-Z	Din	Write to Byte 0 Only
Х	↑	L	Н	Η	Н	L	Н	L	L	High-Z	High-Z	Din	High-Z	Write to Byte 1 Only
Х	↑	L	Н	Ι	L	Н	Н	L	L	High-Z	Din	High-Z	High-Z	Write to Byte 2 Only
Х	↑	L	Н	L	Н	Н	Н	L	L	Din	High-Z	High-Z	High-Z	Write to Byte 3 Only
Х	↑	L	Н	Ι	Н	L	L	L	L	High-Z	High-Z	Din	Din	Write to Lower 2 Bytes Only
Х	1	L	Н	L	L	Н	Н	L	L	Din	Din	High-Z	High-Z	Write to Upper 2 bytes Only
Х	1	L	Н	L	L	L	L	L	L	Din	Din	Din	Din	Write to All Bytes
L	\uparrow	L	Н	Н	Н	Н	L	Н	L	High-Z	High-Z	High-Z	Dout	Read Byte 0 Only
L	1	L	Н	Н	Н	L	Н	Н	L	High-Z	High-Z	Dout	High-Z	Read Byte 1 Only
L	1	L	Н	Н	L	Н	Н	Н	L	High-Z	D оит	High-Z	High-Z	Read Byte 2 Only
L	1	L	Н	L	Н	Н	Н	Н	L	Dout	High-Z	High-Z	High-Z	Read Byte 3 Only
L	↑	L	Н	Η	Н	L	L	Н	L	High-Z	High-Z	Dout	Dout	Read Lower 2 Bytes Only
L	1	L	Н	L	L	Н	Н	Н	L	Dоит	D оит	High-Z	High-Z	Read Upper 2 Bytes Only
L	1	L	Н	L	L	L	L	Н	L	Dout	D оит	Dout	Dout	Read All Bytes
Н	1	Х	Х	Х	Х	Х	Х	Х	L	High-Z	High-Z	High-Z	High-Z	Outputs Disabled
Х	Х	Х	Х	Х	Χ	Χ	Χ	Χ	Н	High-Z	High-Z	High-Z	High-Z	Sleep Mode

5682 tbl 02

NOTES:

- 1. "H" = VIH, "L" = VIL, "X" = Don't Care.
- 2. \overline{ADS} , \overline{CNTEN} , $\overline{REPEAT} = VIH$.
- 3. $\overline{\mathsf{OE}}$ and ZZ are asynchronous input signals.
- 4. It is possible to read or write any combination of bytes during a given access. A few representative samples have been illustrated here.

Truth Table II—Address Counter Control (1,2)

Address	Previous Internal Address	Internal Address Used	CLK	ĀDS	CNTEN	REPEAT ⁽⁶⁾	I/O ⁽³⁾	MODE
An	Х	An	1	L ⁽⁴⁾	Х	Н	Dvo (n)	External Address Used
Х	An	An + 1	1	Н	L ⁽⁵⁾	Н	Di/o(n+1)	Counter Enabled—Internal Address generation ⁽⁷⁾
Х	An + 1	An + 1	1	Н	Н	Н	Di/o(n+1)	External Address Blocked—Counter disabled (An + 1 reused)
Х	Х	An	1	Χ	Х	L ⁽⁴⁾	Di/o(n)	Counter Set to last valid ADS load

NOTES:

- 1. "H" = VIH, "L" = VIL, "X" = Don't Care.
- 2. Read and write operations are controlled by the appropriate setting of R/W, CEo, CE1, BEn and OE.
- 3. Outputs configured in flow-through output mode: if outputs are in pipelined mode the data out will be delayed by one cycle.
- 4. ADS and REPEAT are independent of all other memory control signals including CEo, CE1 and BEn
- 5. The address counter advances if $\overline{\text{CNTEN}} = \text{V}_{\text{IL}}$ on the rising edge of CLK, regardless of all other memory control signals including $\overline{\text{CE}}_0$, CE1, $\overline{\text{BE}}_n$.
- 6. When REPEAT is asserted, the counter will reset to the last valid address loaded via ADS. This value is not set at power-up: a known location should be loaded via ADS during initialization if desired. Any subsequent ADS access during operations will update the REPEAT address location.
- 7. Address A₁₉ must be managed as part of a full depth counter implementation using the IDT70T3509M. For physical addresses 00000H through 7FFFFH the value of a A₁₉ is 0, while for physical addresses 80000H through FFFFFH the value of A₁₉ is 1. The user needs to keep track of the device counter and make sure that A₁₉ is actively driven from 0-to-1 or 1-to-0 and held as needed at the appropriate address boundaries for full depth counter operation and that A₁₉ is in the appropriate state when using the REPEAT function.

Recommended Operating

Temperature and Supply Voltage (1)

Grade	Ambient Temperature	GND	VDD
Commercial	0°C to +70°C	0V	2.5V <u>+</u> 100mV
Industrial	-40°C to +85°C	0V	2.5V <u>+</u> 100mV

NOTES:

5682 tbl 04

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions with VDDQ at 2.5V

Symbol	Parameter	Min.	Тур.	Max.	Unit
VDD	Core Supply Voltage	2.4	2.5	2.6	٧
VDDQ	I/O Supply Voltage ⁽³⁾	2.4	2.5	2.6	V
Vss	Ground	0	0	0	V
Vін	Input High Volltage (Address, Control & Data I/O Inputs) ⁽³⁾	1.7		VDDQ + 100mV ⁽²⁾	>
VIH	Input High Voltage - JTAG	1.7		VDD + 100mV ⁽²⁾	٧
VIН	Input High Voltage - ZZ, OPT, PIPE/FT	VDD - 0.2V		VDD + 100mV ⁽²⁾	٧
V⊩	Input Low Voltage	-0.3 ⁽¹⁾		0.7	٧
VIL	Input Low Voltage - ZZ, OPT, PIPE/FT	-0.3 ⁽¹⁾		0.2	٧

NOTES:

6682 tbl 05a

- 1. V_{IL} (min.) = -1.0V for pulse width less than tcyc/2 or 5ns, whichever is less.
- 2. VIH (max.) = VDDQ + 1.0V for pulse width less than tcyc/2 or 5ns, whichever is less.
- 3. To select operation at 2.5V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to Vss(0V), and VDDOX for that port must be supplied as indicated above.

Recommended DC Operating Conditions with VDDQ at 3.3V

Symbol	Parameter	Min.	Тур.	Max.	Unit
V _{DD}	Core Supply Voltage	Core Supply Voltage 2.4		2.6	V
VDDQ	I/O Supply Voltage (3)	3.15	3.3	3.45	V
Vss	Ground	0	0	0	V
VIH	Input High Voltage (Address, Control &Data I/O Inputs) ⁽³⁾	2.0	2.0 — V		٧
VIH	Input High Voltage - JTAG	1.7		VDD + 100mV ⁽²⁾	٧
VIH	Input High Voltage - ZZ, OPT, PIPE/FT	VDD - 0.2V		VDD + 100mV ⁽²⁾	٧
VIL	Input Low Voltage	-0.3 ⁽¹⁾	_	0.8	V
VIL	Input Low Voltage - ZZ, OPT, PIPE/FT	-0.3 ⁽¹⁾	_	0.2	٧

5682 tbl 05b

- 1. VIL (min.) = -1.0V for pulse width less than tcyc/2, or 5ns, whichever is less.
- 2. Vih (max.) = VDDQ + 1.0V for pulse width less than tcyc/2 or 5ns, whichever is less.
- To select operation at 3.3V levels on the I/Os and controls of a given port, the OPT pin
 for that port must be set to VDD (2.5V), and VDDOX for that port must be supplied as indicated
 above.

Absolute Maximum Ratings (1)

Symbol	Rating	Com'l & Ind	Unit
VTERM (VDD)	V _{DD} Terminal Voltage with Respect to GND	-0.5 to 3.6	V
VTERM ⁽²⁾ (VDDQ)	VDDQ Terminal Voltage with Respect to GND	-0.3 to VDDQ + 0.3	V
V _{TERM} (2) (INPUTS and I/O's)	Input and I/O Terminal Voltage with Respect to GND	-0.3 to VDDQ + 0.3	V
TBIAS ⁽³⁾	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	۰C
NLT	Junction Temperature	+150	°C
IOUT(For VDDQ = 3.3V)	DC Output Current	50	mA
IOUT(For VDDQ = 2.5V)	DC Output Current	40	mA

NOTES:

5682 tbl 06

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause
 permanent damage to the device. This is a stress rating only and functional operation of the
 device at these or any other conditions above those indicated in the operational sections
 of this specification is not implied. Exposure to absolute maximum rating conditions for
 extended periods may affect reliability.
- This is a steady-state DC parameter that applies after the power supply has reached its nominal operating value. Power sequencing is not necessary; however, the voltage on any Input or I/O pin cannot exceed VDDQ during power supply ramp up.
- 3. Ambient Temperature under DC Bias. No AC Conditions. Chip Deselected.

Capacitance⁽¹⁾

(TA = +25°C, F = 1.0MHz) BGA ONLY

Symbol	Parameter	Conditions	Max.	Unit
Cin	Input Capacitance	VIN = 0V	35	pF
Cout ⁽²⁾	Output Capacitance	Vout = 0V	35	pF

NOTES:

5682 tbl 07

- These parameters are determined by device characterization, but are not production tested.
- 2. Cout also references CI/o.

DC Electrical Characteristics Over the Operating

Temperature and Supply Voltage Range (VDD = 2.5V ± 100mV)

			70T3509MS		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Iu	Input Leakage Current ⁽¹⁾	VDDQ = Max., VIN = 0V to VDDQ	_	20	μΑ
Iu	JTAG & ZZ Input Leakage Current ^(1,2)	VDD = Max., VIN = OV to VDD	_	60	μA
lLO	Output Leakage Current ^(1,3)	CE0 = VIH and CE1 = VIL, VOUT = 0V to VDDQ	_	20	μA
Vol (3.3V)	Output Low Voltage ⁽¹⁾	IOL = +4mA, VDDQ = Min.	_	0.4	V
Vон (3.3V)	Output High Voltage ⁽¹⁾	IOH = -4mA, VDDQ = Min.	2.4		V
Vol (2.5V)	Output Low Voltage ⁽¹⁾	IOL = +2mA, VDDQ = Min.	_	0.4	V
Vон (2.5V)	Output High Voltage ⁽¹⁾	IOH = -2mA, VDDQ = Min.	2.0	_	V

NOTES

- 1. VDDQ is selectable (3.3V/2.5V) via OPT pins. Refer to p.5 for details.
- 2. Applicable only for TMS, TDI and TRST inputs.
- 3. Outputs tested in tri-state mode.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (3) (VDD = 2.5V ± 100mV)

					70T3509MS133 Com'l & Ind		
Symbol	Parameter	Test Condition	Versio	n	Typ. ⁽⁴⁾	Max.	Unit
ldd	Dynamic Operating Current (Both	CEL and CER= VIL,	COM'L	S	800	1120	0
	Ports Active)	Outputs Disabled, f = fMAX ⁽¹⁾	IND	S	800	1370	mA
ISB1 ⁽⁶⁾	Standby Current	CEL = CER = VIH	COM'L	S	560	760	m Λ
	(Both Ports - TTL Level Inputs)	$f = fMAX^{(1)}$	IND	S	560	940	mA
ISB2 ⁽⁶⁾	Standby Current (One Port - TTL	CE"A" = VIL and CE"B" = VIH(5)	COM'L	S	680	880	m Λ
	Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	S	680	1090	mA
ISB3	Full Standby Current (Both Ports - CMOS	Both Ports $\overline{CE}OL = \overline{CE}OR \ge VDD - 0.2V$ and	COM'L	S	20	60	mA
	Level Inputs)	CE1L = CE1R \leq 0.2V, VIN \geq VDDQ - 0.2V or VIN \leq 0.2V, f = 0 ⁽²⁾	IND	S	20	80	MA
ISB4 ⁽⁶⁾	Full Standby Current (One Port - CMOS	\overline{CE} "A" $\leq 0.2V$ and \overline{CE} "B" $\geq VDDQ - 0.2V^{(5)}$	COM'L	S	680	880	m Λ
	Level Inputs)	VIN \geq VDDQ - 0.2V or VIN \leq 0.2V Active Port, Outputs Disabled, f = fmax ⁽¹⁾	IND	S	680	1090	mA
lzz	Sleep Mode Current	ZZL = ZZR = VIH $f=fIMAX^{(1)}$	COM'L	S	20	60	mΛ
	(Both Ports - TTL Level Inputs)	I=IMAX` /	IND	S	20	80	mA

- 1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcvc, using "AC TEST CONDITIONS".
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. VDD = 2.5V, TA = 25°C for Typ, and are not production tested. IDD DC(f=0) = 30mA (Typ).
- 5. $\overline{CE}x = VIL \text{ means } \overline{\overline{CE}ox} = VIL \text{ and } CE1x = VIH \text{ (enabled)}$ $\overline{CE}x = VIH \text{ means } \overline{\overline{CE}ox} = VIH \text{ and } CE1x = VIL \text{ (disabled)}$

 - $\label{eq:control_control_control} \begin{array}{l} \overline{CE}x \leq 0.2V \text{ means } \overline{CE}ox \leq 0.2V \text{ and } CE_{1X} \geq VDD \text{ } 0.2V \text{ (enabled CMOS levels)} \\ \overline{CE}x \geq VDD \text{ } 0.2V \text{ means } \overline{CE}ox \geq VDD \text{ } 0.2V \text{ and } CE_{1X} \leq 0.2V \text{ (disabled CMOS levels)} \\ \end{array}$
 - "X" represents "L" for left port or "R" for right port.
- 6. IsB1, IsB2 and IsB4 will all reach full standby levels (IsB3) on the appropriate port(s) if ZZL and/or ZZR = VIH.

AC Test Conditions (VDDQ - 3.3V/2.5V)

10 Test estimitions (VBBQ 3:37/2:37)						
Input Pulse Levels (Address & Controls)	GND to 3.0V/GND to 2.4V					
Input Pulse Levels (I/Os)	GND to 3.0V/GND to 2.4V					
Input Rise/Fall Times	2ns					
Input Timing Reference Levels	1.5V/1.25V					
Output Reference Levels	1.5V/1.25V					
Output Load	Figure 1					

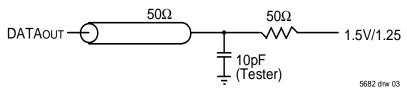
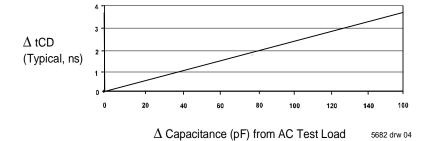


Figure 1. AC Output Test load.



AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) (2,3) (VDD = 2.5V ± 100mV, TA = 0°C to +70°C)

		Co	70T3509MS133 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Unit	
tcyc1	Clock Cycle Time (Flow-Through) ⁽¹⁾	25		ns	
tcyc2	Clock Cycle Time (Pipelined) ⁽¹⁾	7.5		ns	
tcH1	Clock High Time (Flow-Through) ⁽¹⁾	10		ns	
tcl1	Clock Low Time (Flow-Through) ⁽¹⁾	10		ns	
tCH2	Clock High Time (Pipelined) ⁽²⁾	3		ns	
tCL2	Clock Low Time (Pipelined) ⁽¹⁾	3		ns	
tsa	Address Setup Time	1.8		ns	
tha	Address Hold Time	0.5		ns	
tsc	Chip Enable Setup Time	1.8		ns	
thc	Chip Enable Hold Time	0.5		ns	
tsB	Byte Enable Setup Time	1.8		ns	
tнв	Byte Enable Hold Time	0.5		ns	
tsw	R/W Setup Time	1.8		ns	
tHW	R/W Hold Time	0.5		ns	
tsp	Input Data Setup Time	1.8		ns	
thd	Input Data Hold Time	0.5		ns	
tsad	ADS Setup Time	1.8		ns	
thad	ADS Hold Time	0.5		ns	
tscn	CNTEN Setup Time	1.8		ns	
thcn	CNTEN Hold Time	0.5		ns	
tsrpt	REPEAT Setup Time	1.8		ns	
thrpt	REPEAT Hold Time	0.5		ns	
toe	Output Enable to Data Valid		4.6	ns	
tolz ⁽⁴⁾	Output Enable to Output Low-Z	1		ns	
tonz ⁽⁴⁾	Output Enable to Output High-Z	1	4.2	ns	
tcd1	Clock to Data Valid (Flow-Through) ⁽¹⁾		15	ns	
tCD2	Clock to Data Valid (Pipelined) ⁽¹⁾		4.2	ns	
toc	Data Output Hold After Clock High	1		ns	
tckhz ⁽⁴⁾	Clock High to Output High-Z	1	4.2	ns	
tcklz ⁽⁴⁾	Clock High to Output Low-Z	1		ns	
tins	Interrupt Flag Set Time		7	ns	
tinr	Interrupt Flag Reset Time	7	ns		
tcols	Collision Flag Set Time — 4.2				
tcolr	Collision Flag Reset Time — 4.2				
tzzsc	Sleep Mode Set Cycles	2		cycles	
tzzrc	Sleep Mode Recovery Cycles	3		cycles	
Port-to-Port [Delay				
tco	Clock-to-Clock Offset	6		ns	

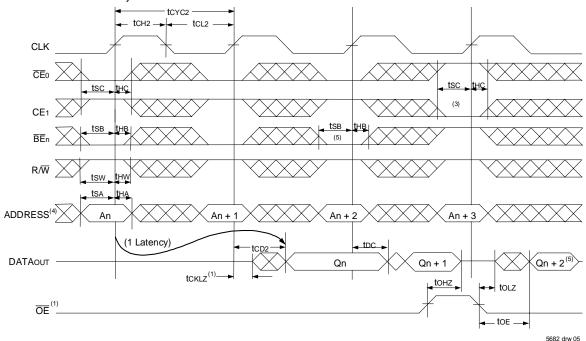
NOTES:

1. The Pipelined output parameters (tcyc2, tcp2) apply to either or both left and right ports when $\overline{FT}/PIPEx = VDD$ (2.5V). Flow-through parameters (tcyc1, tcp1) apply when $\overline{FT}/PIPE = V_{SS}$ (0V) for that port.

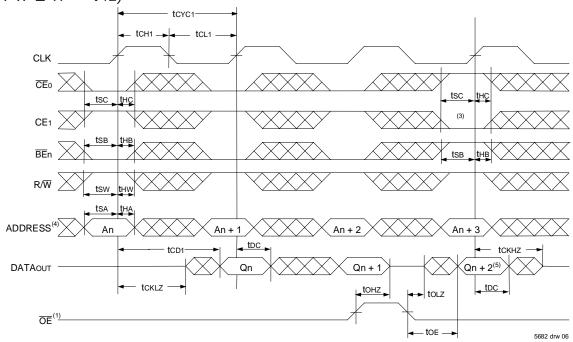
- 3. These values are valid for either level of VDDO (3.3V/2.5V). See page 6 for details on selecting the desired operating voltage levels for each port.
- 4. Guaranteed by design (not production tested).

^{2.} All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE), FT/PIPE and OPT. FT/PIPE and OPT should be treated as DC signals, i.e. steady state during operation.

Timing Waveform of Read Cycle for Pipelined Operation $(FT/PIPE'X' = VIH)^{(1,2)}$

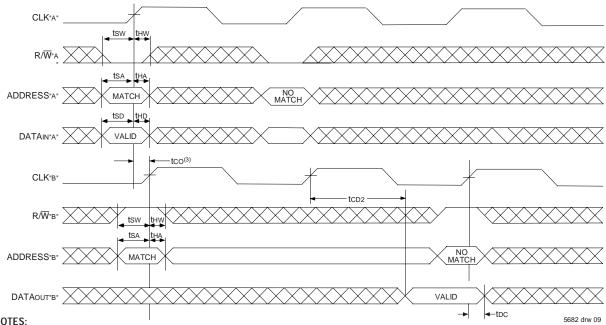


Timing Waveform of Read Cycle for Flow-Through Output $(\mathbf{FT}/PIPE"x" = VIL)^{(1,2,6)}$



- 1. $\overline{\text{OE}}$ is asynchronously controlled; all other inputs depicted in the above waveforms are synchronous to the rising clock edge.
- 2. ADS = VIL, CNTEN and REPEAT = VIH.
- 3. The output is disabled (High-Impedance state) by $\overline{\text{CE}}_0 = \text{V}_{\text{IH}}$, $\text{CE}_1 = \text{V}_{\text{IL}}$, $\overline{\text{BE}}_{\text{n}} = \text{V}_{\text{IH}}$ following the next rising edge of the clock. Refer to Truth Table 1.
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = VIL$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. If BEn was HIGH, then the appropriate Byte of DATAουτ for Qn + 2 would be disabled (High-Impedance state).
- 6. "x" denotes Left or Right port. The diagram is with respect to that port.

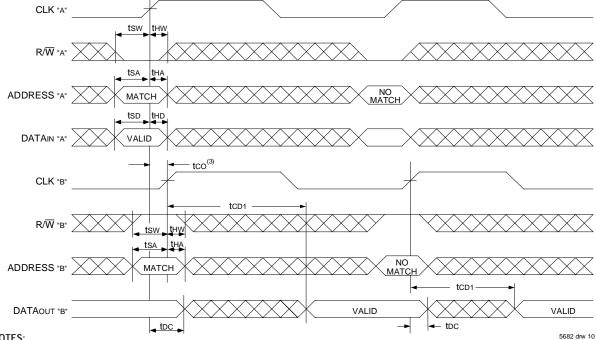
Timing Waveform of Left Port Write to Pipelined Right Port Read (1,2,4)



NOTES:

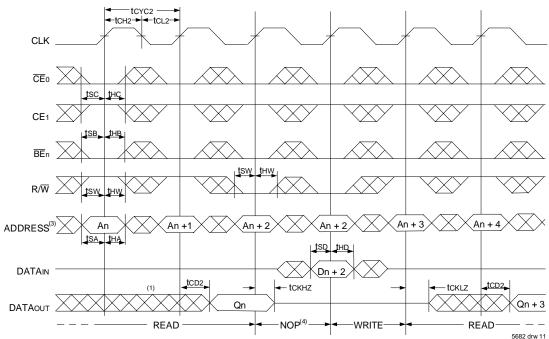
- 1. \overline{CE}_0 , \overline{BE}_n , and $\overline{ADS} = VIL$; CE_1 , \overline{CNTEN} , and $\overline{REPEAT} = VIH$.
- 2. $\overline{OE} = V_{IL}$ for Port "B", which is being read from. $\overline{OE} = V_{IH}$ for Port "A", which is being written to.
- 3. If tco < minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (ie, time from write to valid read on opposite port will be tco + 2 tcyc2 + tcp2). If tco > minimum, then data from Port "B" read is available on first Port "B" clock cycle (ie, time from write to valid read on opposite port
- 4. All timing is the same for Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite of Port "A"

Timing Waveform with Port-to-Port Flow-Through Read (1,2,4)



- 1. \overline{CE}_0 , \overline{BE}_n , and $\overline{ADS} = V_{IL}$; CE_1 , \overline{CNTEN} , and $\overline{REPEAT} = V_{IH}$.
- 2. \overline{OE} = VIL for the Right Port, which is being read from. \overline{OE} = VIH for the Left Port, which is being written to.
- 3. If tco \leq minimum specified, then data from Port "B" read is not valid until following Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tcyc + tcp1). If tco > minimum, then data from Port "B" read is available on first Port "B" clock cycle (i.e., time from write to valid read on opposite port will be tco + tcD1).
- 4. All timing is the same for both left and right ports. Port "A" may be either left or right port. Port "B" is the opposite of Port "A".

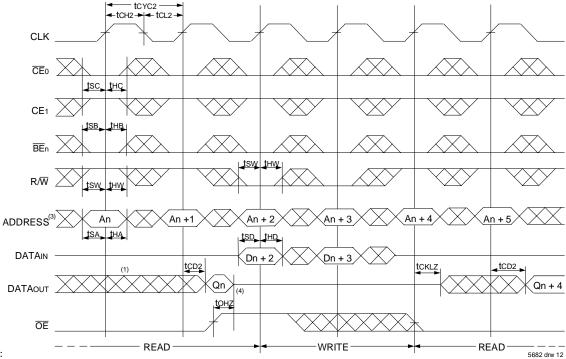
Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** = VIL)(2)



NOTES:

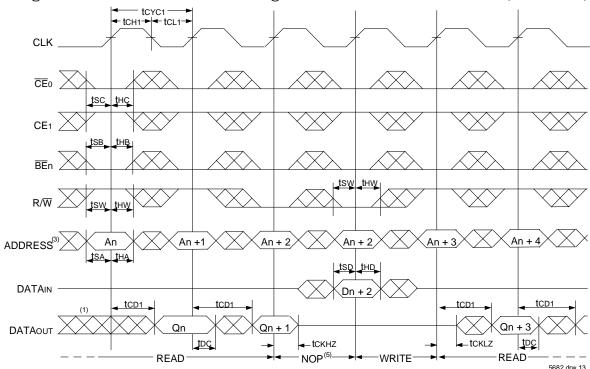
- Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
 \overline{CE0}, \overline{BEn}, and \overline{ADS} = VIL; CE1, \overline{CNTEN}, and \overline{REPEAT} = VIH. "NOP" is "No Operation".
- Addresses do not have to be accessed sequentially since ADS = Vil. constantly loads the address on the rising edge of the CLK; numbers
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to quarantee data integrity.

Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽²⁾

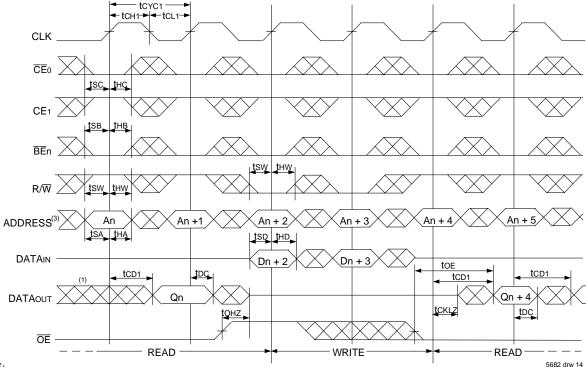


- Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- CEo, BEn, and ADS = VIL; CE1, CNTEN, and REPEAT = VIH.
- Addresses do not have to be accessed sequentially since ADS = Vil. constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- This timing does not meet requirements for fastest speed grade. This waveform indicates how logically it could be done if timing so allows.

Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** = VIL)⁽²⁾

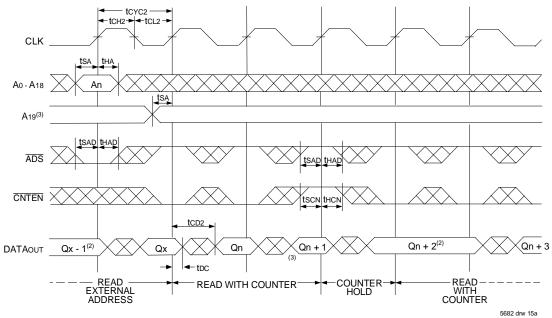


Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** Controlled)⁽²⁾

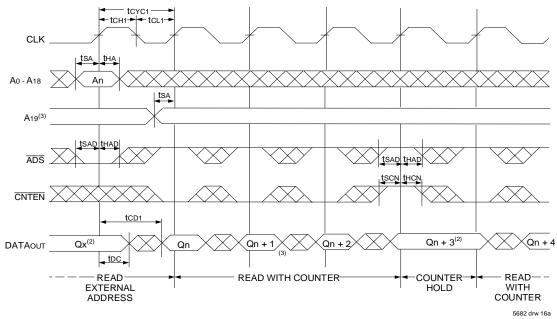


- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 2. $\overline{\text{CE}}_0$, $\overline{\text{BE}}_n$, and $\overline{\text{ADS}} = \text{ViL}$; $\overline{\text{CE}}_1$, $\overline{\text{CNTEN}}$, and $\overline{\text{REPEAT}} = \text{ViH}$.
- 3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾

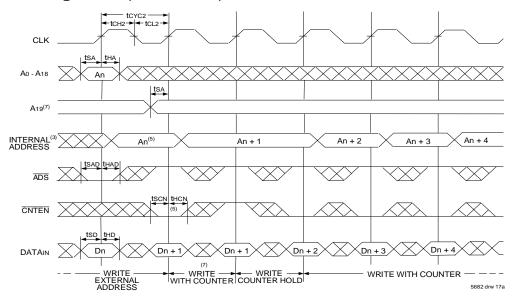


Timing Waveform of Flow-Through Read with Address Counter Advance (1)

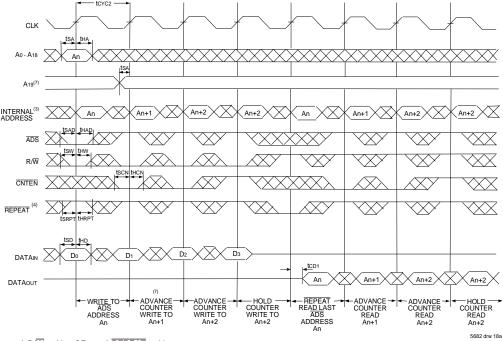


- 1. \overline{CE}_0 , \overline{OE} , \overline{BE}_0 = VIL; CE1, R/ \overline{W} , and \overline{REPEAT} = VIH.
- 2. If there is no address change via $\overline{ADS} = V_{IL}$ (loading a new address) or $\overline{CNTEN} = V_{IL}$ (advancing the address), i.e. $\overline{ADS} = V_{IH}$ and $\overline{CNTEN} = V_{IH}$, then the data remains constant for subsequent clocks.
- 3. Address A19 must be managed as part of a full depth counter implementation using the IDT70T3509M. For physical addresses 00000H through 7FFFFH the value of a A19 is 0, while for physical addresses 80000H through FFFFFH the value of A19 is 1. The user needs to keep track of the device counter and make sure that A19 is actively driven from 0-to-1 or 1-to-0 and held as needed at the appropriate address boundaries for full depth counter operation. As shown this transition reflects An = 7FFFFH or FFFFFH.

Timing Waveform of Write with Address Counter Advance (Flow-through or Pipelined Inputs)⁽¹⁾

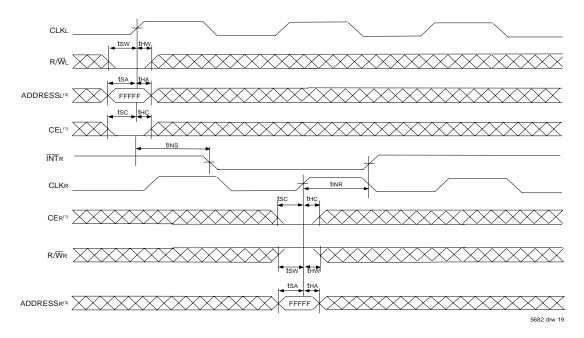


Timing Waveform of Counter Repeat (2,6)



- 1. $\overline{CE_0}$, $\overline{BE_n}$, and $R/\overline{W} = VIL$; CE_1 and $\overline{REPEAT} = VIH$.
- 2. \overline{CE}_0 , $\overline{BE}_n = VIL$; $CE_1 = VIH$.
- 3. The "Internal Address" is equal to the "External Address" when \overline{ADS} = VIL and equals the counter output when \overline{ADS} = VIH.
- 4. No dead cycle exists during REPEAT operation. A READ or WRITE cycle may be coincidental with the counter REPEAT cycle: Address loaded by last valid ADS load will be accessed. For more information on REPEAT function refer to Truth Table II. A19 must be in the appropriate state when using the REPEAT function to guarantee the correct address location is loaded.
- 5. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1'Address is written to during this cycle.
- 6. For Pipelined Mode user should add 1 cycle latency for outputs as per timing waveform of read cycle for pipelined operations.
- 7. Address A19 must be managed as part of a full depth counter implementation using the IDT70T3509M. For physical addresses 00000H through 7FFFFH the value of a A19 is 0, while for physical addresses 80000H through FFFFFH the value of A19 is 1. The user needs to keep track of the device counter and make sure that A19 is actively driven from 0-to-1 or 1-to-0 and held as needed at the appropriate address boundaries for full depth counter operation. As shown this transition reflects An = 7FFFFH or FFFFFH.

Waveform of Interrupt Timing⁽²⁾



NOTES:

- 1. $\overline{CE}_0 = V_{IL}$ and $CE_1 = V_{IH}$.
- 2. All timing is the same for Left and Right ports.
- 3. Address is for internal register, not the external bus, i.e. address needs to be qualified by one of the Address counter control signals.

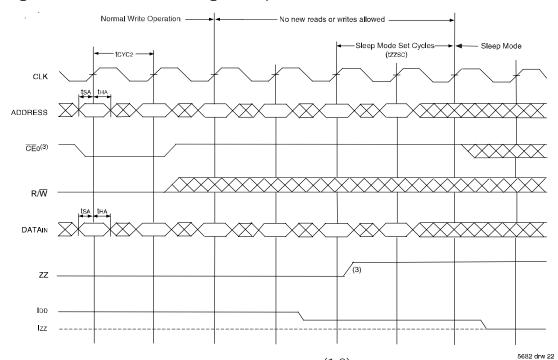
Truth Table III - Interrupt Flag⁽¹⁾

	Left Port					Right Port				
CLKL	R/WL ⁽²⁾	CEL ⁽²⁾	A19L-A0L	ĪNTL	CLKR	R/WR ⁽²⁾	CER ⁽²⁾	A19R-A0R	ĪNĪr	Function
1	L	L	FFFFF	Χ	1	Х	Χ	Х	L	Set Right INTR Flag
1	Х	Х	Х	Х	1	Н	L	FFFFF	Н	Reset Right INTR Flag
1	Х	Х	Х	L	1	L	L	FFFFE	Х	Set Left INTL Flag
1	Н	L	FFFFE	Н	1	Х	Х	Χ	Х	Reset Left INTL Flag

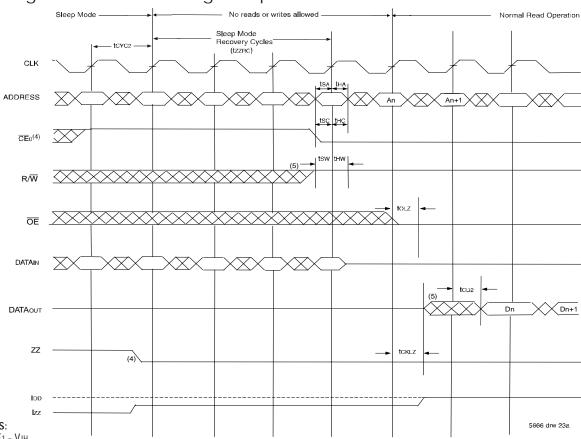
5682 tbl 12

- 1. \overline{INT}_L and \overline{INT}_R must be initialized at power-up by Resetting the flags.
- 2. $\overline{\text{CE}}_0 = \text{V}_{\text{IL}}$ and $\text{CE}_1 = \text{V}_{\text{IH}}$, R/\overline{W} and $\overline{\text{CE}}$ are synchronous with respect to the clock and need valid set-up and hold times.
- 3. Address is for internal register, not the external bus, i.e. address needs to be qualified by one of the Address counter control signals.

Timing Waveform - Entering Sleep Mode (1,2)



Timing Waveform - Exiting Sleep Mode (1,2)



NOTES: 1. CE1 = VIH.

- 2. All timing is same for Left and Right ports.
- \overline{CE}_0 has to be deactivated $\overline{(CE}_0 = V_{IH})$ three cycles prior to asserting ZZ (ZZx = V_{IH}) and held for two cycles after asserting ZZ (ZZx = V_{IH}). \overline{CE}_0 has to be deactivated $\overline{(CE}_0 = V_{IH})$ one cycle prior to de-asserting ZZ (ZZx = V_{IL}) and held for three cycles after de-asserting ZZ (ZZx = V_{IL}).
- The device must be in Read Mode (R/W High) when exiting sleep mode. Outputs are active but data is not valid until the following cycle.

Functional Description

The IDT70T3509M provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse width is independent of the cycle time.

An asynchronous output enable is provided to ease asynchronous bus interfacing. Counterenable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

The combination of a HIGHon $\overline{\text{CE}}$ o and a LOW on CE1 for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70T3509Ms for depth expansion configurations. Two cycles are required with $\overline{\text{CE}}$ 0 LOW and CE1 HIGH to re-activate the outputs.

Width Expansion

The IDT70T3509M can be used in applications requiring expanded width. Through combining the control signals, the devices can be grouped as necessary to accommodate applications needing 72-bits or wider.

Sleep Mode

The IDT70T3509M is equipped with an optional sleep or low power mode on both ports. The sleep mode pin on both ports is asynchronous and active high. During normal operation, the ZZ pin is pulled low. When ZZ is pulled high, the port will enter sleep mode where it will meet lowest possible power conditions. The sleep mode timing diagram shows the modes of operation: Normal Operation, No Read/Write Allowed and Sleep Mode

For normal operation all inputs must meet setup and hold times prior to sleep and after recovering from sleep. Clocks must also meet cycle high and low times during these periods. Three cycles prior to asserting ZZ (ZZx = VIH) and three cycles after de-asserting ZZ (ZZx = VIL), the device must be disabled via the chip enable pins. If a write or read operation occurs during these periods, the memory array may be corrupted. Validity of data out from the RAM cannot be guaranteed immediately after ZZ is asserted (prior to being in sleep). When exiting sleep mode, the device must be in Read mode (R/ \overline{W} x = VIH) when chip enable is asserted, and the chip enable must be valid for one full cycle before a read will result in the output of valid data.

During sleep mode the RAM automatically deselects itself. The RAM disconnects its internal clock buffer. The external clock may continue to run without impacting the RAMs sleep current (Izz). All outputs will remain in high-Z state while in sleep mode. All inputs are allowed to toggle. The RAM will not be selected and will not perform any reads or writes.

JTAG Functionality and Configuration

The IDT70T3509M is composed of four independent memory arrays, and thus cannot be treated as a single JTAG device in the scan chain. The four arrays (A, B, C and D) each have identical characteristics and commands but must be treated as separate entities in JTAG operations. Please refer to Figure 2.

JTAG signaling must be provided serially to each array and utilize the information provided in the Identification Register Definitions, Scan

Register Sizes, and System Interface Parameter tables. Specifically, all serial commands must be issued to the IDT70T3509M in the following sequence: Array D, Array C, Array B, Array A. Please reference Application Note AN-411, "JTAG Testing of Multichip Modules" for specific instructions on performing JTAG testing on the IDT70T3509M. AN-411 is available at www.idt.com.

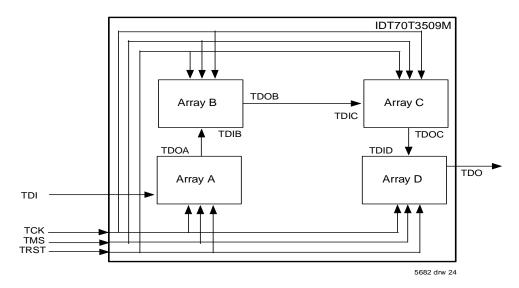
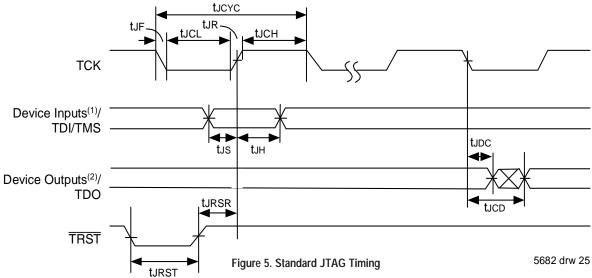


Figure 2. JTAG Configuration for IDT70T3509M

JTAG Timing Specifications



NOTES:

- 1. Device inputs = All device inputs except TDI, TMS, and TRST.
- 2. Device outputs = All device outputs except TDO.

JTAG AC Electrical Characteristics (1,2,3,4)

		70T3509M		
Symbol	Parameter	Min.	Мах.	Units
ticyc	JTAG Clock Input Period	100	_	ns
tлсн	JTAG Clock HIGH	40	_	ns
tıcı	JTAG Clock Low	40		ns
tır	JTAG Clock Rise Time		3 ⁽¹⁾	ns
tur	JTAG Clock Fall Time		3 ⁽¹⁾	ns
URST	JTAG Reset	50		ns
URSR	JTAG Reset Recovery	50	_	ns
tuco	JTAG Data Output	_	25	ns
tupc	JTAG Data Output Hold	0	_	ns
tus	JTAG Setup	15	_	ns
tлн	JTAG Hold	15	_	ns

NOTES:

- 1. Guaranteed by design.
- 2. 30pF loading on external output signals.
- 3. Refer to AC Electrical Test Conditions stated earlier in this document.
- 4. JTAG operations occur at one speed (10MHz). The base device may run at any speed specified in this datasheet.

Identification Register Definitions

Instruction Field Array D	Value Array D	Instruction Field Array C	Value Array C	Instruction Field Array B	Value Array B	Instruction Field Array A	Value Array A	Description
Revision Number (31:28)	0x0	Revision Number (63:60)	0x0	Revision Number (95:92)	0x0	Revision Number (127:124)	0x0	Reserved for Version number
IDT Device ID (27:12)	0x333	IDT Device ID (59:44)	0x333	IDT Device ID (91:76)	0x333	IDT Device ID (123:108)	0x333	Defines IDT Part number
IDT JEDEC ID (11:1)	0x33	IDT JEDEC ID (43:33)	0x33	IDT JEDEC ID (75:65)	0x33	IDT JEDEC ID (107:97)	0x33	Allows unique identification of device vendor as IDT
ID Register Indicator Bit (Bit 0)	1	ID Register Indicator Bit (Bit 32)	1	ID Register Indicator Bit (Bit 64)	1	ID Register Indicator Bit (Bit 96)	1	Indicates the presence of an ID Register

5682 thl 16

Scan Register Sizes

Register Name	Bit Size Array A	Bit Size Array B	Bit Size Array C	Bit Size Array D	Bit Size 70T3509M
Instruction (IR)	4	4	4	4	16
Bypass (BYR)	1	1	1	1	4
Identification (IDR)	32	32	32	32	128
Boundary Scan (BSR)	Note (3)				

5682 tbl 17

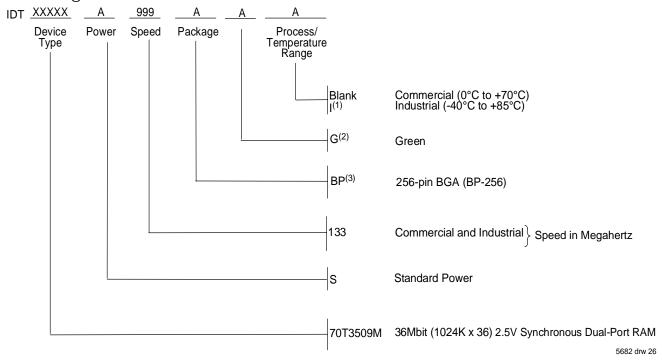
System Interface Parameters

Instruction	Code	Description				
EXTEST 00000000000000 F		Forces contents of the boundary scan cells onto the device outputs ⁽¹⁾ . Places the boundary scan register (BSR) between TDI and TDO.				
BYPASS	111111111111111	Places the bypass register (BYR) between TDI and TDO.				
IDCODE	0010001000100010	Loads the ID register (IDR) with the vendor ID code and places the register between TDI and TDO.				
HIGHZ	0100010001000100	Places the bypass register (BYR) between TDI and TDO. Forces all device output drivers except INTx to a High-Z state.				
CLAMP	0011001100110011	Uses BYR. Forces contents of the boundary scan cells onto the device outputs. Places the bypass register (BYR) between TDI and TDO.				
SAMPLE/PRELOAD	0001000100010001	Places the boundary scan register (BSR) between TDI and TDO. SAMPLE allows data from device inputs ⁽²⁾ to be captured in the boundary scan cells and shifted serially through TDO. PRELOAD allows data to be input serially into the boundary scan cells via the TDI.				
RESERVED	01010101010101010, 0111011101110111, 10001000	Several combinations are reserved. Do not use codes other than those identified above.				
PRIVATE	0110011001100110,1110111011101110, 11011101	For internal use only.				

5682 tbl 18

- 1. Device outputs = All device outputs except TDO.
- 2. Device inputs = All device inputs except TDI, TMS, and $\overline{\text{TRST}}$.
- 3. The Boundary Scan Descriptive Language (BSDL) file for this device is available on the IDT website (www.idt.com), or by contacting your local IDT sales representative.

Ordering Information



NOTES:

- 1. Contact your local sales office for Industrial temp range in other speeds, packages and powers.
- 2. Green parts available. For specific speeds, packages and powers contact your local sales office.
- 3. BP-256 package thickness is 1.76mm nominal. This is thicker than the BC-256 package (1.40mm nominal) used for the lower density IDT dual-port products.

Datasheet Document History:

11/09/04: Initial Public Release of Preliminary Datasheet 03/24/05: Page 1 Added I-temp offering to features

Page 6 Added I-temp information to the Recommended Operating Temperature and Supply Voltage table

Page 8 Added I-temp values to the DC Electrical Characteristics table

Page 10 Added I-temp to the heading of the AC Electrical Characteristics table

Page 23 Added I-temp to ordering information Page 1 Added green availability to features Page 1 - 23 Removed Preliminary status

06/14/05: Page 1 Added feature to highlight footprint compatibility

Page 3 & 23 Added a footnote to highlight package thickness of BP-256 vs. BC-256

08/27/07: Page 1 Functional Block Diagram changed to correct chip enable logic and added footnote 2 referencing Truth Table I



CORPORATE HEADQUARTERS

6024 Silver Creek Valley Road San Jose, CA 95138

for SALES:

800-345-7015 or 408-284-8200 fax: 408-284-2775 www.idt.com

for Tech Support: 408-284-2794 DualPortHelp@idt.com

The IDT logo is a registered trademark of Integrated Device Technology, Inc.